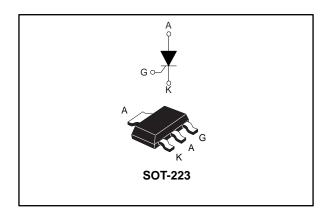
# **P0111MN**



# Sensitive 0.8 A SCR thyristor

Datasheet - production data



#### **Features**

- I<sub>T(RMS)</sub> 0.8 A
- 125 °C max T<sub>i</sub>
- Low 0.004 to 0.025 mA gate current
- 600 V V<sub>DRM</sub>/V<sub>RRM</sub>
- ECOPACK®2 compliant component

### **Applications**

- Proximity sensors
- Gate driver for large thyristors
- Overvoltage crowbar protection
- Ground fault circuit interrupters
- Arc fault circuit interrupter
- Solid state relay pilot circuit
- Standby mode power supplies
- Residual current detector

### **Description**

Thanks to highly sensitive triggering levels, the 0.8 A P0111MN SCR thyristor is suitable for all applications where available gate current is limited. This device offers a high blocking voltage of 600 V, ideal for applications like interrupters circuits.

The surface mount SOT-223 package allows compact, SMD based designs for automated manufacturing.

**Table 1: Device summary** 

| Symbol                             | Value          | Unit |
|------------------------------------|----------------|------|
| I <sub>T(RMS)</sub>                | 0.8            | Α    |
| V <sub>DRM</sub> /V <sub>RRM</sub> | 600            | V    |
| l <sub>GT</sub>                    | 0.004 to 0.025 | mA   |
| T <sub>j</sub> max.                | 125            | °C   |

Characteristics P0111MN

# 1 Characteristics

Table 2: Absolute maximum ratings (limiting values), T<sub>j</sub> = 25 °C unless otherwise specified

| Symbol                             | Parameter   |                         |                          | Value            | Unit |
|------------------------------------|---|-------------------------|--------------------------|------------------|------|
| I <sub>T(RMS)</sub>                | RMS on-state current (180 ° cond  |                         | 0.8                      |                  |      |
| I <sub>T(AV)</sub>                 | Average on-state current (180 ° conduction angle)   |                         | T <sub>amb</sub> = 70 °C | 0.5              | А    |
| I                                  | Non repetitive surge peak on-state  | e current               | $t_p = 8.3 \text{ ms}$   | 8                | Α    |
| IISM                               | (T <sub>j</sub> initial = 25 °C)  |                         | $t_p = 10 \text{ ms}$    | 7                | A    |
| l <sup>2</sup> t                   | I <sup>2</sup> t value for fusing   | $t_p = 10 \text{ ms}$   | 0.24                     | A <sup>2</sup> s |      |
| dl/dt                              | Critical rate of rise of on-state current $f = 60 \text{ Hz}$ $f = 60 \text{ Hz}$ $f = 60 \text{ Hz}$ |                         | T <sub>j</sub> = 125 °C  | 50               | A/µs |
| V <sub>DRM</sub> /V <sub>RRM</sub> | Repetitive peak off-state voltage   |                         | T <sub>j</sub> = 125 °C  | 600              | V    |
| l <sub>GM</sub>                    | Peak gate current   | t <sub>p</sub> = 20 μs  | T <sub>j</sub> = 125 °C  | 1                | Α    |
| P <sub>G(AV)</sub>                 | Average gate power dissipation  | T <sub>j</sub> = 125 °C | 0.1                      | W                |      |
| T <sub>stg</sub>                   | Storage junction temperature range  |                         |                          | -40 to +150      | °C   |
| Tj                                 | Operating junction temperature  |                         | -40 to +125              | °C               |      |

Table 3: Electrical characteristics ( $T_j = 25$  °C unless otherwise specified)

| Symbol           | Test conditions  |      | Value    | Unit |          |                |    |
|------------------|--|------|----------|------|----------|----------------|----|
| I <sub>GT</sub>  | V 40 V D 440 O   |      | Min Max. |      | Min Max. | 0.004 to 0.025 | mA |
| V <sub>G</sub> T | $V_D = 12 \text{ V}, R_L = 140 \Omega$                     |      | Max.     | 0.8  | V        |                |    |
| $V_{GD}$         | $V_D = V_{DRM},~R_L = 3.3~k\Omega,~R_{GK} = 1000~\Omega$   | Min. | 0.1      | V    |          |                |    |
| $V_{RG}$         | $I_{RG} = 10 \mu A$  |      | Min.     | 8    | V        |                |    |
| Ін               | $I_T$ = 50 mA, $R_{GK}$ = 1000 $\Omega$                    | Max. | 5        | mA   |          |                |    |
| IL               | $I_{G} = 1.2 \text{ x } I_{GT}, R_{GK} = 1000 \Omega$      |      | Max.     | 6    | mA       |                |    |
| dV/dt            | $V_D = 67 \% V_{DRM}, R_{GK} = 1000 \Omega$ $T_j = 125 °C$ |      | Min.     | 80   | V/µs     |                |    |

**Table 4: Static characteristics** 

| Symbol                 | Test conditions   |                         |      | Value | Unit |
|------------------------|---|-------------------------|------|-------|------|
| V <sub>TM</sub>        | $I_{TM} = 1.6 \text{ A}, t_p = 380 \ \mu s$ $T_j = 25 \ ^{\circ}C$ Max. |                         | Max. | 1.95  | V    |
| Vто                    | Threshold voltage   | T <sub>j</sub> = 125 °C | Max. | 0.95  | V    |
| R₀                     | Dynamic resistance  | T <sub>j</sub> = 125 °C | Max. | 600   | mΩ   |
| 1 /1                   | $V_D = V_{DRM}, V_R = V_{RRM},$   |                         | Mex  | 10    |      |
| $R_{GK} = 1000 \Omega$ |   | T <sub>j</sub> = 125 °C | Max. | 100   | μA   |

**Table 5: Thermal parameters** 

| Symbol               | Paramete                 | Value                      | Unit |      |
|----------------------|--------------------------|----------------------------|------|------|
| R <sub>th(j-t)</sub> | Junction to tab (DC)     |                            | 30   |      |
| R <sub>th(j-a)</sub> | Junction to ambient (DC) | $S^{(1)} = 5 \text{ cm}^2$ | 60   | °C/W |

**Notes:** (1)S = copper surface under tab.



P0111MN Characteristics

# 1.1 Characteristics (curves)

Figure 1: Maximum average power dissipation versus average on-state current

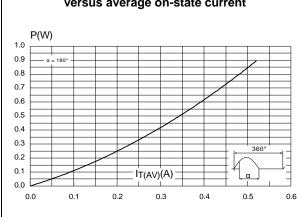


Figure 2: Average and DC on-state current versus case temperature  $I_{T(AV)}(A)$ 1.0 0.9 0.8 0.7 0.6  $\alpha = 180^{\circ} (SOT-223)$ 0.5 0.4 0.3 0.2 0.1 T<sub>lead</sub> (°C) 0.0 25 50 125 ٥ 100

Figure 3: Average and DC on-state current versus ambient temperature

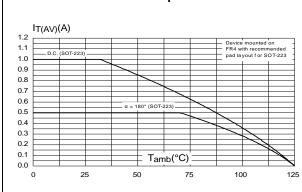


Figure 4: Relative variation of thermal impedance versus pulse duration

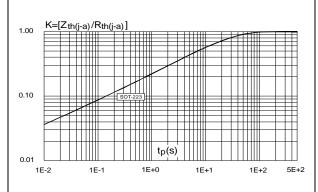


Figure 5: Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)

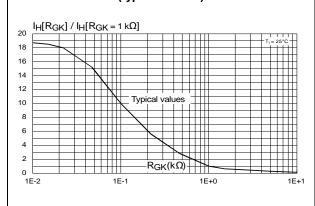
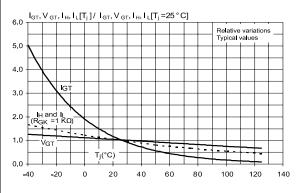


Figure 6: Relative variation of holding and latching current versus junction temperature (typical values)



Characteristics P0111MN

immunity versus gate-cathode resistance (typical values)

dV/dt[R<sub>GK</sub>] / dV/dt[R<sub>GK</sub> = 1kΩ]

1.0

Typical values

1.0

R<sub>GK</sub>(kΩ)

0.1

0.2

0.4

0.6

0.8

1.0

1.2

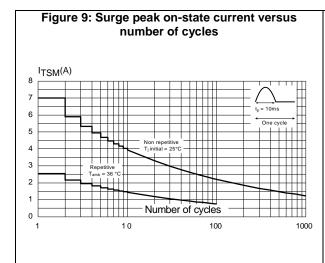
1.4

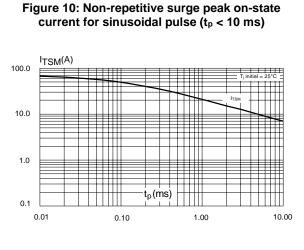
1.6

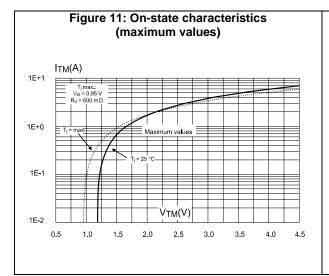
1.8

2.0

Figure 7: Relative variation of static dV/dt







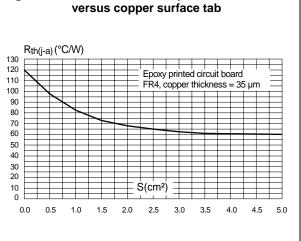


Figure 12: Thermal resistance junction to ambient

P0111MN Package information

# 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Lead-free package
- Halogen free molding resin
- Epoxy meets UL94, V0

# 2.1 SOT-223 package information

Figure 13: SOT-223 package outline

D
B1
12
3
0046067\_14

Table 6: SOT-223 package mechanical data

| Dim.             | Millimeters |      |      |        | Inches <sup>(1)</sup> |        |
|------------------|-------------|------|------|--------|-----------------------|--------|
| Dilli.           | Min.        | Тур. | Max. | Min.   | Тур.                  | Max.   |
| А                |             |      | 1.8  |        |                       | 0.0709 |
| A1               | 0.02        |      | 0.1  | 0.0008 |                       | 0.0039 |
| В                | 0.6         | 0.7  | 0.85 | 0.0236 | 0.0276                | 0.0335 |
| B1               | 2.9         | 3    | 3.15 | 0.1142 | 0.1181                | 0.1240 |
| С                | 0.24        | 0.26 | 0.35 | 0.0094 | 0.0102                | 0.0138 |
| D <sup>(2)</sup> | 6.3         | 6.5  | 6.7  | 0.2480 | 0.2559                | 0.2638 |
| е                |             | 2.3  |      |        | 0.0906                |        |
| e1               |             | 4.6  |      |        | 0.1811                |        |
| E                | 3.3         | 3.5  | 3.7  | 0.1299 | 0.1378                | 0.1457 |
| Н                | 6.7         | 7.0  | 7.3  | 0.2638 | 0.2756                | 0.2874 |
| V                |             |      | 10°  |        |                       | 10°    |

#### Notes:

3.3 6.4 (3x)1.5 4.6 0046067

Figure 14: SOT-223 recommended footprint (dimensions are in mm)

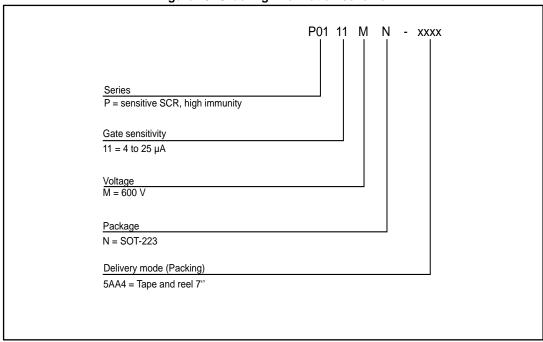
<sup>&</sup>lt;sup>(1)</sup>Inches dimensions given only for reference

 $<sup>^{(2)}</sup>$ Does not include mold flash or protusions. Mold flash or protusions must not exceed 0.15 mm (0.006 inches)

P0111MN Ordering information

# 3 Ordering information

Figure 15: Ordering information scheme



**Table 7: Ordering information** 

| Order code   | Marking | Package | Weight | Base qty. | Delivery mode    |
|--------------|---------|---------|--------|-----------|------------------|
| P0111MN 5AA4 | P1M     | SOT-223 | 0.12 g | 1000      | Tape and reel 7" |

# 4 Revision history

**Table 8: Document revision history** 

| Date        | Revision | Changes          |
|-------------|----------|------------------|
| 09-Oct-2017 | 1        | Initial release. |

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